

TOSHIBA**TC74LCX14F/FN/FT**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74LCX14F, TC74LCX14FN, TC74LCX14FT**LOW VOLTAGE HEX SCHMITT INVERTER
WITH 5V TOLERANT INPUTS AND OUTPUTS**

The TC74LCX14 is a high performance CMOS SCHMITT INVERTER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for inputs.

Pin configuration and function are the same as the TC74LCX04 but the inputs have hysteresis and with its schmitt trigger function, the TC74LCX14 can be used as a line receivers which will receive slow input signals.

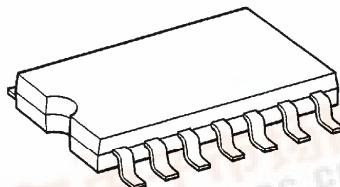
All inputs are equipped with protection circuits against static discharge.

FEATURES

- Low voltage operation : V_{CC} = 2.0~3.6V
- High speed operation : t_{pd} = 6.5ns (Max.) (V_{CC} = 3.0~3.6V)
- Output current : |I_{OH}| / |I_{OL}| = 24mA (Min.) (V_{CC} = 3.0V)
- Latch-up performance : ± 500mA
- Available in JEDEC SOP, EIAJ SOP and TSSOP
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series (74AC/VHC/HC/F/ALS/LS etc.) 14 type.

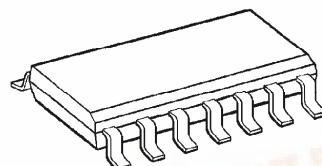
(Note) The JEDEC SOP (FN) is not available in Japan.

TC74LCX14F



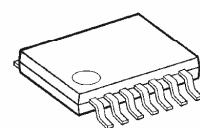
SOP14-P-300-1.27

TC74LCX14FN



SOL14-P-150-1.27

TC74LCX14FT



TSSOP14-P-0044-0.65

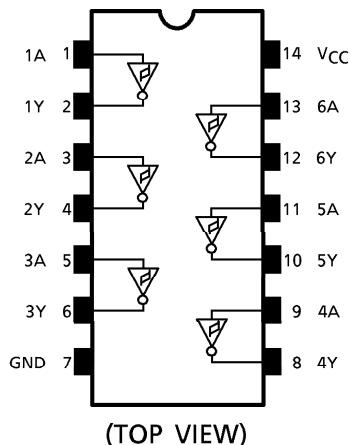
Weight

SOP14-P-300-1.27	: 0.18g (Typ.)
SOL14-P-150-1.27	: 0.12g (Typ.)
TSSOP14-P-0044-0.65	: 0.06g (Typ.)

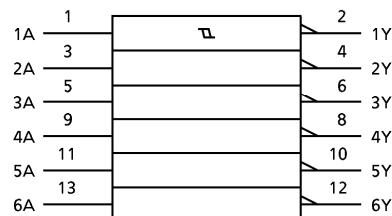
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PIN ASSIGNMENT



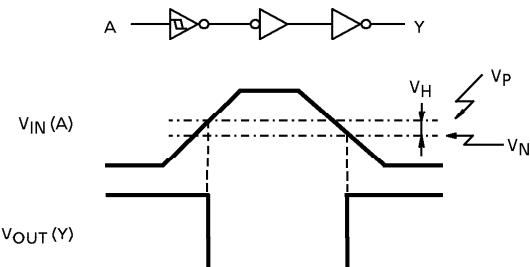
IEC LOGIC SYMBOL



TRUTH TABLE

INPUTS	OUTPUTS
A	Y
L	H
H	L

SYSTEM DIAGRAM, WAVEFORM



MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V _{CC}	-0.5~7.0	V
DC Input Voltage	V _{IN}	-0.5~7.0	V
DC Output Voltage	V _{OUT}	-0.5~7.0 (Note 1)	V
		-0.5~V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IK}	-50	mA
Output Diode Current	I _{OK}	±50 (Note 3)	mA
DC Output Current	I _{OUT}	±50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} / Ground Current	I _{CC} / I _{GND}	±100	mA
Storage Temperature	T _{stg}	-65~150	°C

(Note 1) V_{CC} = 0V

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 3) V_{OUT} < GND, V_{OUT} > V_{CC}

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- The information contained herein is subject to change without notice.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~5.5 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH} / I_{OL}	± 24 (Note 7)	mA
		± 12 (Note 8)	
Operating Temperature	T_{opr}	-40~85	°C

(Note 4) Data Retention Only

(Note 5) $V_{CC} = 0V$

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0 \sim 3.6V$ (Note 8) $V_{CC} = 2.7 \sim 3.0V$

ELECTRICAL CHARACTERISTICS

DC CHARACTERISTICS ($T_a = -40 \sim 85^\circ C$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT	
Threshold Voltage	"H" Level	V_P	$V_{IN} = V_{IL}$	$I_{OH} = -100\mu A$	3.0	1.2	2.2	V	
	"L" Level	V_N			3.0	0.6	1.5		
Hysteresis Voltage	V_H					3.0	0.4	1.2	
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IL}$	$I_{OH} = -100\mu A$	2.7~3.6	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -12mA$	2.7	2.2	—		
				$I_{OH} = -18mA$	3.0	2.4	—		
				$I_{OH} = -24mA$	3.0	2.2	—		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$	$I_{OL} = 100\mu A$	2.7~3.6	—	0.2	V	
				$I_{OL} = 12mA$	2.7	—	0.4		
				$I_{OL} = 16mA$	3.0	—	0.4		
				$I_{OL} = 24mA$	3.0	—	0.55		
Input Leakage Current	I_{IN}	$V_{IN} = 0 \sim 5.5V$		2.7~3.6		—	± 5.0	μA	
Power Off Leakage Current	I_{OFF}	$V_{IN} / V_{OUT} = 5.5V$		0		—	10.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7~3.6		—	10.0	μA	
		$V_{IN} / V_{OUT} = 3.6 \sim 5.5V$		2.7~3.6		—	± 10.0		
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6V$		2.7~3.6		—	500	μA	

AC CHARACTERISTICS ($T_a = -40\sim85^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	MIN.	MAX.	UNIT
Propagation Delay Time	t_{pLH}	(Fig. 1, 2)	2.7	—	7.5	ns
	t_{pHL}		3.3 ± 0.3	1.5	6.5	
Output To Output Skew	t_{osLH}	(Note 9)	2.7	—	—	ns
	t_{osHL}		3.3 ± 0.3	—	1.0	

(Note 9) Parameter guaranteed by design.
 $(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$

DYNAMIC SWITCHING CHARACTERISTICS ($T_a = 25^\circ C$, Input $t_r = t_f = 2.5\text{ns}$, $C_L = 50\text{pF}$, $R_L = 500\Omega$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$V_{IH} = 3.3\text{V}, V_{IL} = 0\text{V}$	3.3	0.8	V
Quiet Output Minimum Dynamic V_{OL}	$ V_{OLV} $	$V_{IH} = 3.3\text{V}, V_{IL} = 0\text{V}$	3.3	0.8	V

CAPACITIVE CHARACTERISTICS ($T_a = 25^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP	UNIT	
Input Capacitance	C_{IN}	—	3.3	7	pF	
	C_{OUT}		0			
Power Dissipation Capacitance	C_{PD}	$f_{IN} = 10\text{MHz}$	(Note 10)	3.3	25	pF

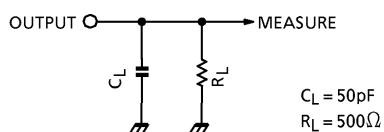
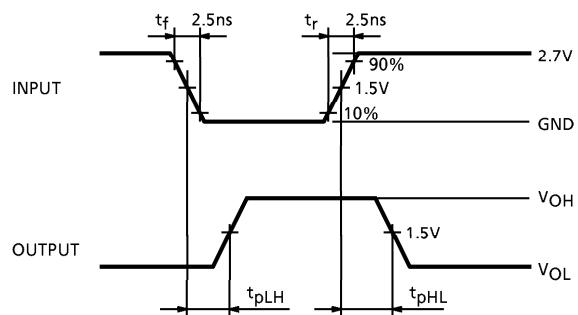
(Note 10) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 6 \text{ (Per gate)}$$

TEST CIRCUIT

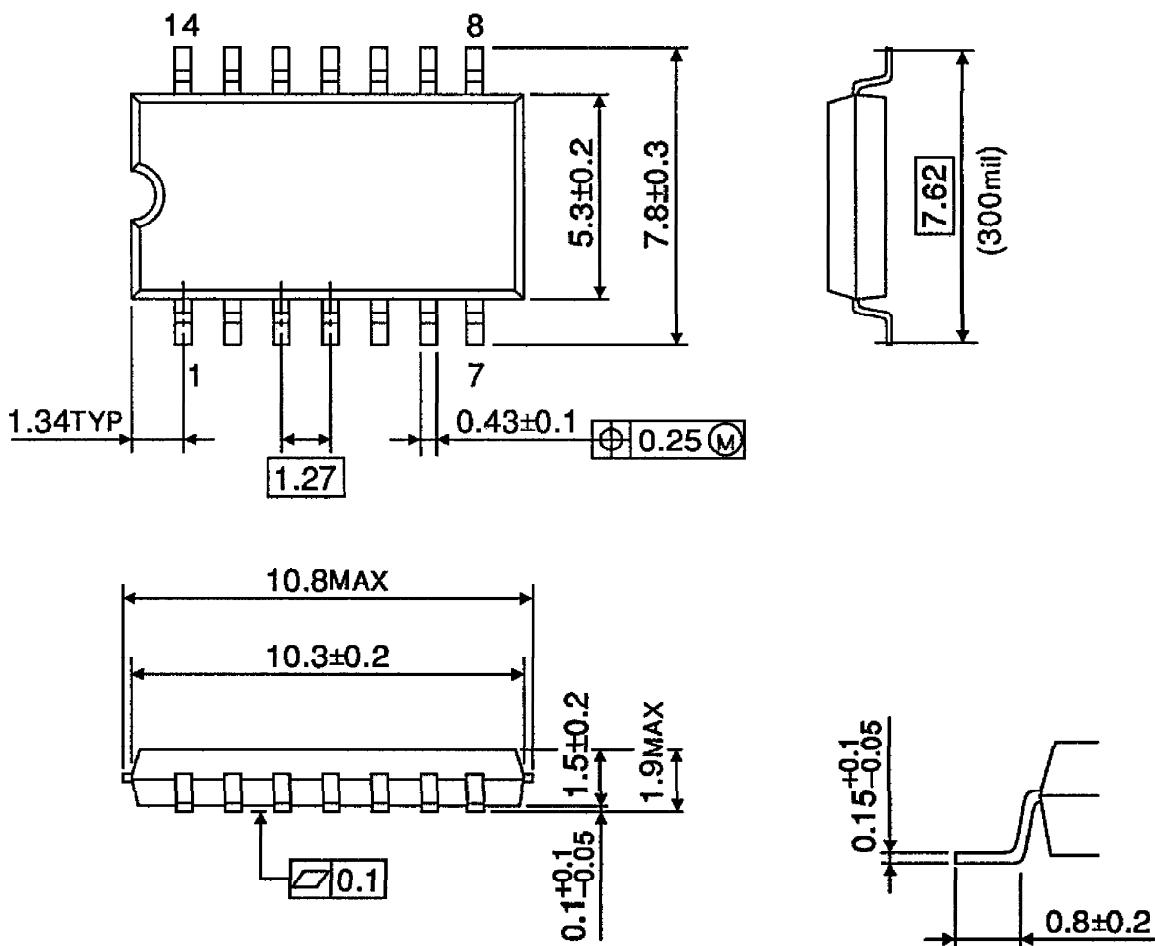
Fig.1

**AC WAVEFORM**Fig.2 t_{pLH} , t_{pHL} 

OUTLINE DRAWING

SOP14-P-300-1.27

Unit : mm

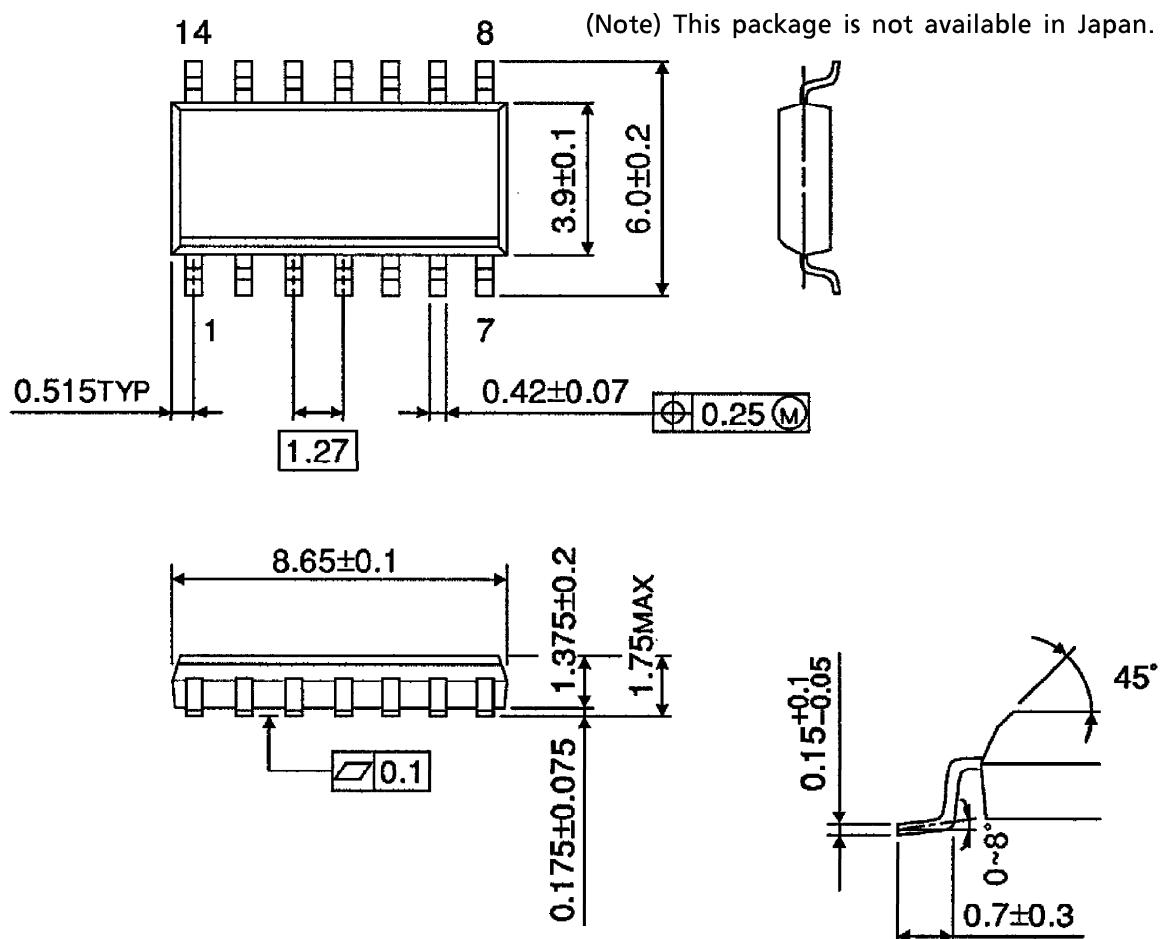


Weight : 0.18g (Typ.)

OUTLINE DRAWING

SOL14-P-150-1.27

UNIT : mm

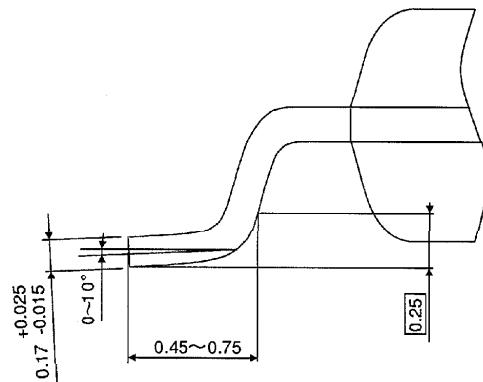
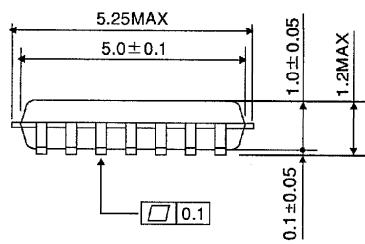
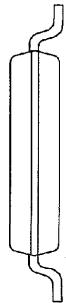
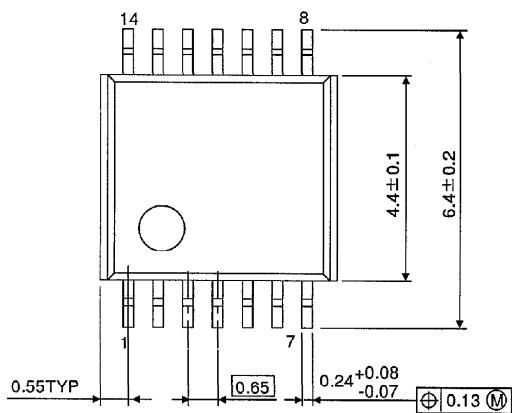


Weight : 0.12g (Typ.)

OUTLINE DRAWING

TSSOP14-P-0044-0.65

Unit : mm



Weight : 0.06g (Typ.)